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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	34
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s207s6t3c

List of tables

Independent watchdog timer

The independent watchdog peripheral can be used to resolve processor malfunctions due to hardware or software failures.

It is clocked by the 128 kHz LSI internal RC clock source, and thus stays active even in case of a CPU clock failure

The IWDG time base spans from 60 µs to 1 s.

4.8 Auto wakeup counter

- Used for auto wakeup from active halt mode
- Clock source: Internal 128 kHz internal low frequency RC oscillator or external clock
- LSI clock can be internally connected to TIM3 input capture channel 1 for calibration

4.9 Beeper

The beeper function outputs a signal on the BEEP pin for sound generation. The signal is in the range of 1, 2 or 4 kHz.

4.10 TIM1 - 16-bit advanced control timer

This is a high-end timer designed for a wide range of control applications. With its complementary outputs, dead-time control and center-aligned PWM capability, the field of applications is extended to motor control, lighting and half-bridge driver

- 16-bit up, down and up/down autoreload counter with 16-bit prescaler
- Four independent capture/compare channels (CAPCOM) configurable as input capture, output compare, PWM generation (edge and center aligned mode) and single pulse mode output
- Synchronization module to control the timer with external signals
- Break input to force the timer outputs into a defined state
- Three complementary outputs with adjustable dead time
- Encoder mode
- Interrupt sources: 3 x input capture/output compare, 1 x overflow/update, 1 x break

4.11 TIM2, TIM3 - 16-bit general purpose timers

- 16-bit autoreload (AR) up-counter
- 15-bit prescaler adjustable to fixed power of 2 ratios 1…32768
- Timers with 3 or 2 individually configurable capture/compare channels
- PWM mode
- Interrupt sources: 2 or 3 x input capture/output compare, 1 x overflow/update

Table 6. Pin description (continued)

Pin number					Pin name	Type	Input			Output				Main function (after reset)	Default alternate function	Alternate function after remap [option bit]
LQFP80	LQFP64	LQFP48	LQFP44	LQFP32			floating	wpu	Ext. interrupt	High sink	Speed	OD	PP			
46	37	29	-	21	PC4/TIM1_CH4	I/O	X	X	X	HS	O3	X	X	**Port C4**	Timer 1 - channel 4	
47	38	30	27	22	PC5/SPI_SCK	I/O	X	X	X	HS	O3	X	X	**Port C5**	SPI clock	
48	39	31	28	-	V_{SSIO_2}	S								I/O ground		
49	40	32	29	-	V_{DDIO_2}	S								I/O power supply		
50	41	33	30	23	PC6/SPI_MOSI	I/O	X	X	X	HS	O3	X	X	**Port C6**	SPI master out/ slave in	
51	42	34	31	24	PC7/SPI_MISO	I/O	X	X	X	HS	O3	X	X	**Port C7**	SPI master in/ slave out	
52	43	35	32	-	PG0/CAN_TX(2)	I/O	X	X			O1	X	X	**Port G0**	beCAN transmit	
53	44	36	33	-	PG1/CAN_RX(2)	I/O	X	X			O1	X	X	**Port G1**	beCAN receive	
54	45	-	-	-	PG2	I/O	X	X			O1	X	X	**Port G2**		
55	46	-	-	-	PG3	I/O	X	X			O1	X	X	**Port G3**		
56	47	-	-	-	PG4	I/O	X	X			O1	X	X	**Port G4**		
57	48	-	-	-	PI0	I/O	X	X			O1	X	X	**Port I0**		
58	-	-	-	-	PI1	I/O	X	X			O1	X	X	**Port I1**		
59	-	-	-	-	PI2	I/O	X	X			O1	X	X	**Port I2**		
60	-	-	-	-	PI3	I/O	X	X			O1	X	X	**Port I3**		
61	-	-	-	-	PI4	I/O	X	X			O1	X	X	**Port I4**		
62	-	-	-	-	PI5	I/O	X	X			O1	X	X	**Port I5**		
63	49	-	-	-	PG5	I/O	X	X			O1	X	X	**Port G5**		
64	50	-	-	-	PG6	I/O	X	X			O1	X	X	**Port G6**		
65	51	-	-	-	PG7	I/O	X	X			O1	X	X	**Port G7**		
66	52	-	-	-	PE4	I/O	X	X	X		O1	X	X	**Port E4**		
67	53	37	-	-	PE3/TIM1_BKIN	I/O	X	X	X		O1	X	X	**Port E3**	Timer 1 - break input	
68	54	38	34	-	PE2/I^2C_SDA	I/O	X		X		O1	T(3)		**Port E2**	I^2C data	

remap) option bits. Refer to *Section 8: Option bytes on page 47*. When the remapping option is active, the default alternate function is no longer available.

To use an alternate function, the corresponding peripheral must be enabled in the peripheral registers.

Alternate function remapping does not effect GPIO capabilities of the I/O ports (see the GPIO section of the family reference manual, RM0016).

Table 9. General hardware register map

Address	Block	Register label	Register name	Reset status
0x00 5050 to 0x00 5059	Reserved area (10 bytes)			
0x00 505A	Flash	FLASH_CR1	Flash control register 1	0x00
0x00 505B		FLASH_CR2	Flash control register 2	0x00
0x00 505C		FLASH_NCR2	Flash complementary control register 2	0xFF
0x00 505D		FLASH _FPR	Flash protection register	0x00
0x00 505E		FLASH _NFPR	Flash complementary protection register	0xFF
0x00 505F		FLASH _IAPSR	Flash in-application programming status register	0x00
0x00 5060 to 0x00 5061	Reserved area (2 bytes)			
0x00 5062	Flash	FLASH _PUKR	Flash Program memory unprotection register	0x00
0x00 5063	Reserved area (1 byte)			
0x00 5064	Flash	FLASH _DUKR	Data EEPROM unprotection register	0x00
0x00 5065 to 0x00 509F	Reserved area (59 bytes)			
0x00 50A0	ITC	EXTI_CR1	External interrupt control register 1	0x00
0x00 50A1		EXTI_CR2	External interrupt control register 2	0x00
0x00 50A2 to 0x00 50B2	Reserved area (17 bytes)			
0x00 50B3	RST	RST_SR	Reset status register	0xXX(1)
0x00 50B4 to 0x00 50BF	Reserved area (12 bytes)			
0x00 50C0	CLK	CLK_ICKR	Internal clock control register	0x01
0x00 50C1		CLK_ECKR	External clock control register	0x00
0x00 50C2	Reserved area (1 byte)			
0x00 50C3	CLK	CLK_CMSR	Clock master status register	0xE1
0x00 50C4		CLK_SWR	Clock master switch register	0xE1
0x00 50C5		CLK_SWCR	Clock switch control register	0xXX
0x00 50C6		CLK_CKDIVR	Clock divider register	0x18
0x00 50C7		CLK_PCKENR1	Peripheral clock gating register 1	0xFF
0x00 50C8		CLK_CSSR	Clock security system register	0x00
0x00 50C9		CLK_CCOR	Configurable clock control register	0x00
0x00 50CA		CLK_PCKENR2	Peripheral clock gating register 2	0xFF
0x00 50CB		CLK_CANCCR	CAN clock control register	0x00

8 Option bytes

Option bytes contain configurations for device hardware features as well as the memory protection of the device. They are stored in a dedicated block of the memory. Except for the ROP (read-out protection) byte, each option byte has to be stored twice, in a regular form (OPTx) and a complemented one (NOPTx) for redundancy.

Option bytes can be modified in ICP mode (via SWIM) by accessing the EEPROM address shown in *Table 12: Option bytes* below. Option bytes can also be modified 'on the fly' by the application in IAP mode, except the ROP option that can only be modified in ICP mode (via SWIM).

Refer to the STM8S Flash programming manual (PM0051) and STM8 SWIM communication protocol and debug module user manual (UM0470) for information on SWIM programming procedures.

Table 12. Option bytes

Addr.	Option name	Option byte no.	Option bits								Factory default setting
			7	6	5	4	3	2	1	0	
4800h	Read-out protection (ROP)	OPT0	ROP[7:0]								00h
4801h	User boot code (UBC)	OPT1	UBC[7:0]								00h
4802h		NOPT1	NUBC[7:0]								FFh
4803h	Alternate function remapping (AFR)	OPT2	AFR7	AFR6	AFR5	AFR4	AFR3	AFR2	AFR1	AFR0	00h
4804h		NOPT2	NAFR7	NAFR6	NAFR5	NAFR4	NAFR3	NAFR2	NAFR1	NAFR0	FFh
4805h	Watchdog option	OPT3	Reserved				LSI _EN	IWDG _HW	WWDG _HW	WWDG _HALT	00h
4806h		NOPT3	Reserved				NLSI _EN	NIWDG _HW	NWWDG _HW	NWWDG _HALT	FFh
4807h	Clock option	OPT4	Reserved				EXT CLK	CKAWU SEL	PRS C1	PRS C0	00h
4808h		NOPT4	Reserved				NEXT CLK	NCKAWU SEL	NPR SC1	NPR SC0	FFh
4809h	HSE clock startup	OPT5	HSECNT[7:0]								00h
480Ah		NOPT5	NHSECNT[7:0]								FFh
480Bh	Reserved	OPT6	Reserved								00h
480Ch		NOPT6	Reserved								FFh
480Dh	Flash wait states	OPT7	Reserved							Wait state	00h
480Eh		NOPT7	Reserved							Nwait state	FFh
487Eh	Bootloader	OPTBL	BL[7:0]								00h
487Fh		NOPTBL	NBL[7:0]								FFh

Table 16. Current characteristics

Symbol	Ratings	Max.[(1)]	Unit
I_{VDD}	Total current into V_{DD} power lines (source)[(2)]	60	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)[(2)]	60	
I_{IO}	Output current sunk by any I/O and control pin	20	
	Output current source by any I/Os and control pin	20	
ΣI_{IO}	Total output current sourced (sum of all I/O and control pins) for devices with two V_{DDIO} pins[(3)]	200	
	Total output current sourced (sum of all I/O and control pins) for devices with one V_{DDIO} pin[(3)]	100	
	Total output current sunk (sum of all I/O and control pins) for devices with two V_{SSIO} pins[(3)]	160	
	Total output current sunk (sum of all I/O and control pins) for devices with one V_{SSIO} pin[(3)]	80	
$I_{INJ(PIN)}$[(4)(5)]	Injected current on NRST pin	±4	
	Injected current on OSCIN pin	±4	
	Injected current on any other pin[(6)]	±4	
$\Sigma I_{INJ(PIN)}$[(4)]	Total injected current (sum of all I/O and control pins)[(6)]	±20	

1. Data based on characterization results, not tested in production.
2. All power (V_{DD}, V_{DDIO}, V_{DDA}) and ground (V_{SS}, V_{SSIO}, V_{SSA}) pins must always be connected to the external supply.
3. I/O pins used simultaneously for high current source/sink must be uniformly spaced around the package between the V_{DDIO}/V_{SSIO} pins.
4. $I_{INJ(PIN)}$ must never be exceeded. This is implicitly insured if V_{IN} maximum is respected. If V_{IN} maximum cannot be respected, the injection current must be limited externally to the $I_{INJ(PIN)}$ value. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. For true open-drain pads, there is no positive injection current, and the corresponding V_{IN} maximum must always be respected
5. Negative injection disturbs the analog performance of the device. See note in *Section 10.3.10: 10-bit ADC characteristics on page 85*.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with $\Sigma I_{INJ(PIN)}$ maximum current injection on four I/O port pins of the device.

Table 17. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-65 to 150	°C
T_J	Maximum junction temperature	150	

10.3.2 Supply current characteristics

The current consumption is measured as described in *Figure 9 on page 52*.

Total current consumption in run mode

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled (clock stopped by Peripheral Clock Gating registers) except if explicitly mentioned.
- When the MCU is clocked at 24 MHz, $T_A \leq 105$ °C and the WAITSTATE option bit is set.

Subject to general operating conditions for V_{DD} and T_A.

Table 20. Total current consumption with code execution in run mode at V_{DD} = 5 V

Symbol	Parameter	Conditions		Typ	Max	Unit
$I_{DD(RUN)}$	Supply current in run mode, code executed from RAM	$f_{CPU} = f_{MASTER}$ = 24 MHz, $T_A \leq$ 105 °C	HSE crystal osc. (24 MHz)	4.4		mA
			HSE user ext. clock (24 MHz)	3.7	7.3(1)	
		$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	3.3		
			HSE user ext. clock (16 MHz)	2.7	5.8	
			HSI RC osc. (16 MHz)	2.5	3.4	
		$f_{CPU} = f_{MASTER}$/128 = 125 kHz	HSE user ext. clock (16 MHz)	1.2	4.1(1)	
			HSI RC osc. (16 MHz)	1.0	1.3(1)	
		$f_{CPU} = f_{MASTER}$/128 = 15.625 kHz	HSI RC osc. (16 MHz/8)	0.55		
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.45		
	Supply current in run mode, code executed from Flash	$f_{CPU} = f_{MASTER}$ = 24 MHz, $T_A \leq$ 105 °C	HSE crystal osc. (24 MHz)	11.4		
			HSE user ext. clock (24 MHz)	10.8	18(1)	
		$f_{CPU} = f_{MASTER}$ = 16 MHz	HSE crystal osc. (16 MHz)	9.0		
			HSE user ext. clock (16 MHz)	8.2	15.2(1)	
			HSI RC osc.(16 MHz)	8.1	13.2(1)	
		$f_{CPU} = f_{MASTER}$ = 2 MHz.	HSI RC osc. (16 MHz/8)(2)	1.5		
		$f_{CPU} = f_{MASTER}$/128 = 125 kHz	HSI RC osc. (16 MHz)	1.1		
		$f_{CPU} = f_{MASTER}$/128 = 15.625 kHz	HSI RC osc. (16 MHz/8)	0.6		
		$f_{CPU} = f_{MASTER}$ = 128 kHz	LSI RC osc. (128 kHz)	0.55		

1. Data based on characterization results, not tested in production.
2. Default clock configuration measured with all peripherals off.

10.3.3 External clock sources and timing characteristics

HSE user external clock

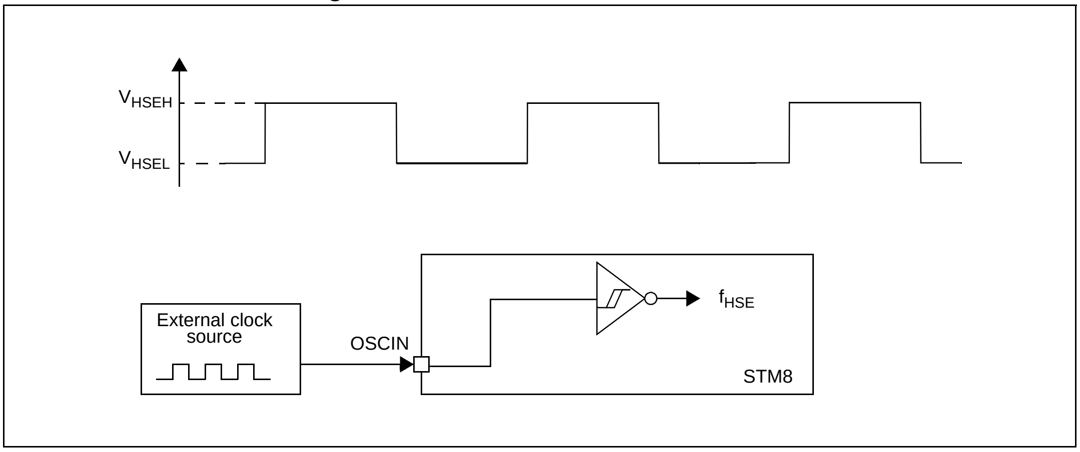
Subject to general operating conditions for V_{DD} and T_A.

Table 31. HSE user external clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency		0		24	MHz
V_{HSEH}(1)	OSCIN input pin high level voltage		0.7 x V_{DD}		V_{DD} + 0.3 V	V
V_{HSEL}(1)	OSCIN input pin low level voltage		V_{SS}		0.3 x V_{DD}	V
I_{LEAK_HSE}	OSCIN input leakage current	$V_{SS} < V_{IN} < V_{DD}$	-1		1	µA

1. Data based on characterization results, not tested in production.

Figure 16. HSE external clock source



HSE crystal/ceramic resonator oscillator

The HSE clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph is based on characterization results with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal resonator manufacturer for more details (frequency, package, accuracy...).

10.3.5 Memory characteristics

RAM and hardware registers

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Unit
V_{RM}	Data retention mode(1)	Halt mode (or reset)	V_{IT-max}(2)	V

1. Minimum supply voltage without losing data stored in RAM (in halt mode or under reset) or in hardware registers (only in halt mode). Guaranteed by design, not tested in production.
2. Refer to *Table 19 on page 57* for the value of V_{IT-max}.

Flash program memory/data EEPROM memory

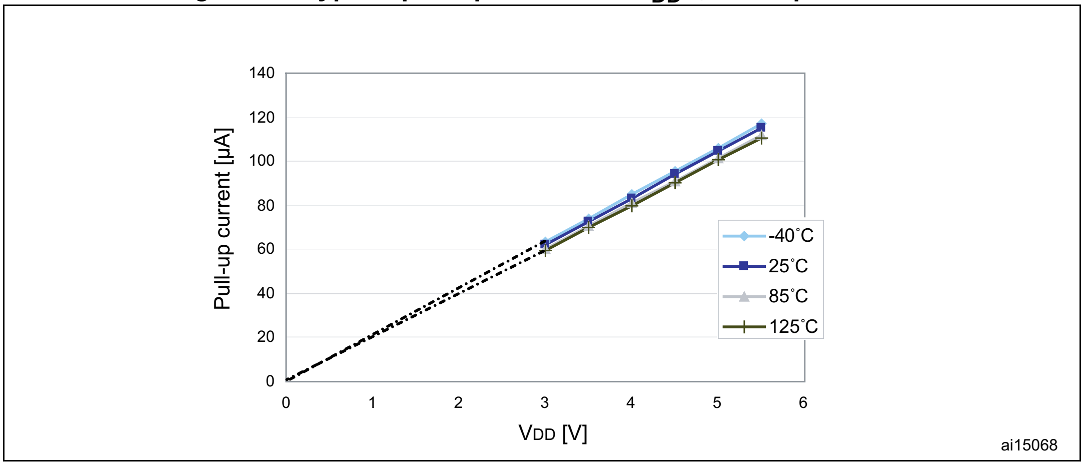
General conditions: T_A = -40 to 125 °C.

Table 36. Flash program memory/data EEPROM memory

Symbol	Parameter	Conditions	Min(1)	Typ	Max	Unit
V_{DD}	Operating voltage (all modes, execution/write/erase)	$f_{CPU} \leq$ 24 MHz	2.95		5.5	V
t_{prog}	Standard programming time (including erase) for byte/word/block (1 byte/4 bytes/128 bytes)			6	6.6	ms
	Fast programming time for 1 block (128 bytes)			3	3.3	ms
t_{erase}	Erase time for 1 block (128 bytes)			3	3.3	ms
N_{RW}	Erase/write cycles(2) (program memory)	T_A = 85 °C	10 k			cycles
	Erase/write cycles (data memory)(2)	T_A = 125 ° C	300 k	1M		
t_{RET}	Data retention (program memory) after 10 k erase/write cycles at T_A = 85 °C	T_{RET} = 55° C	20			years
	Data retention (data memory) after 10 k erase/write cycles at T_A = 85 °C	T_{RET} = 55° C	20			
	Data retention (data memory) after 300k erase/write cycles at T_A = 125 °C	T_{RET} = 85° C	1			
I_{DD}	Supply current (Flash programming or erasing for 1 to 128 bytes)			2		mA

1. Data based on characterization results, not tested in production.
2. The physical granularity of the memory is 4 bytes, so cycling is performed on 4 bytes even when a write/erase operation addresses a single byte.

Figure 22. Typical pull-up current vs V_{DD} @ 4 temperatures



1. The pull-up is a pure resistor (slope goes through 0).

Table 38. Output driving current (standard ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V		2	V
	Output low level with 4 pins sunk	I_{IO} = 4 mA, V_{DD} = 3.3 V		1(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO} = 10 mA, V_{DD} = 5 V	2.8		V
	Output high level with 4 pins sourced	I_{IO} = 4 mA, V_{DD} = 3.3 V	2.1(1)		

1. Data based on characterization results, not tested in production

Table 39. Output driving current (true open drain ports)

Symbol	Parameter	Conditions	Max	Unit
V_{OL}	Output low level with 2 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V	1	V
		I_{IO} = 10 mA, V_{DD} = 3.3 V	1.5(1)	
		I_{IO} = 20 mA, V_{DD} = 5 V	2(1)	

1. Data based on characterization results, not tested in production

Table 40. Output driving current (high sink ports)

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level with 8 pins sunk	I_{IO} = 10 mA, V_{DD} = 5 V		0.8	V
	Output low level with 4 pins sunk	I_{IO} = 10 mA, V_{DD} = 3.3 V		1(1)	
	Output low level with 4 pins sunk	I_{IO} = 20 mA, V_{DD} = 5 V		1.5(1)	
V_{OH}	Output high level with 8 pins sourced	I_{IO} = 10 mA, V_{DD} = 5 V	4.0		
	Output high level with 4 pins sourced	I_{IO} = 10 mA, V_{DD} = 3.3 V	2.1(1)		
	Output high level with 4 pins sourced	I_{IO} = 20 mA, V_{DD} = 5 V	3.3(1)		

1. Data based on characterization results, not tested in production

Figure 34. Typical NRST pull-up resistance vs V_{DD} @ 4 temperatures

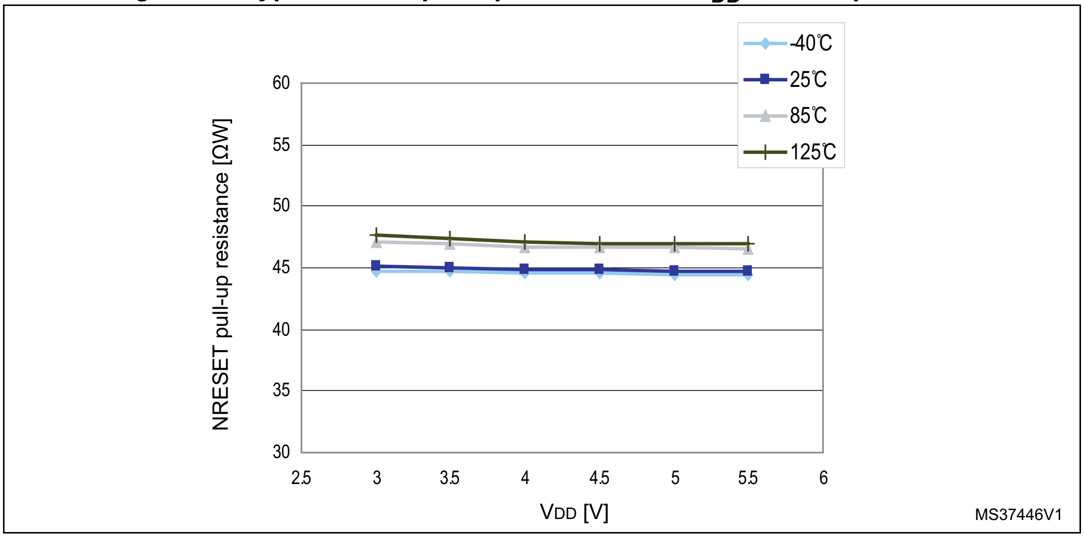
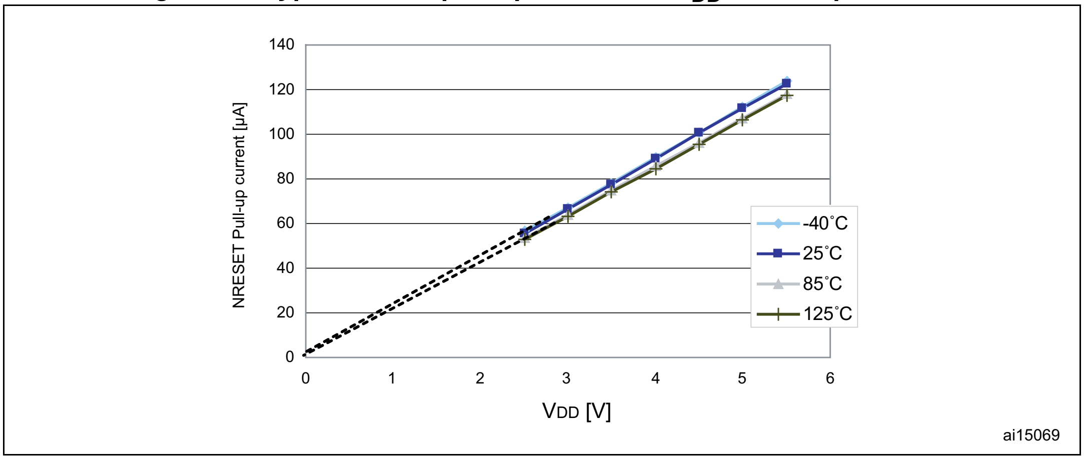
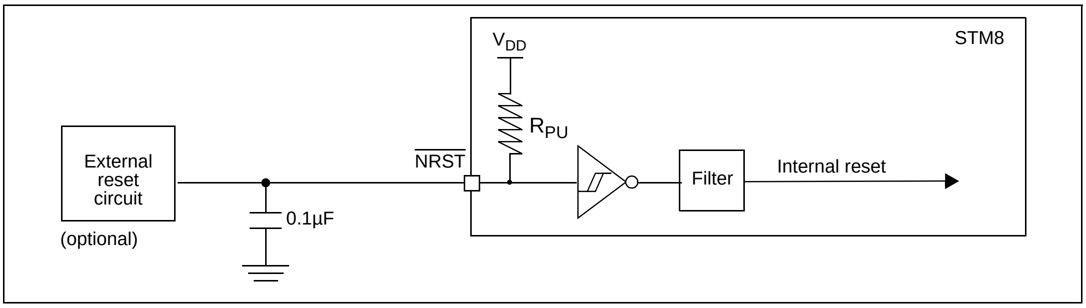


Figure 35. Typical NRST pull-up current vs V_{DD} @ 4 temperatures



The reset network shown in *Figure 36* protects the device against parasitic resets. The user must ensure that the level on the NRST pin can go below the V_{IL} max. level specified in *Table 41*. Otherwise the reset is not taken into account internally. For power consumption sensitive applications, the capacity of the external reset capacitor can be reduced to limit charge/discharge current. If the NRSTsignal is used to reset the external circuitry, care must be taken of the charge/discharge time of the external capacitor to fulfill the external device's reset timing conditions. The minimum recommended capacity is 10 nF.

Figure 36. Recommended reset pin protection



10.3.8 SPI serial peripheral interface

Unless otherwise specified, the parameters given in *Table 42* are derived from tests performed under ambient temperature, f_{MASTER} frequency and V_{DD} supply voltage conditions. $t_{MASTER} = 1/f_{MASTER}$.

Refer to I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 42. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode	0	10	MHz
		Slave mode	0	6	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF		25	ns
$t_{su(NSS)}$[1]	NSS setup time	Slave mode	4 x t_{MASTER}		
$t_{h(NSS)}$[1]	NSS hold time	Slave mode	70		
$t_{w(SCKH)}$[1] $t_{w(SCKL)}$[1]	SCK high and low time	Master mode	$t_{SCK}/2 - 15$	$t_{SCK}/2 + 15$	
$t_{su(MI)}$[1] $t_{su(SI)}$[1]	Data input setup time	Master mode	5		
		Slave mode	5		
$t_{h(MI)}$[1] $t_{h(SI)}$[1]	Data input hold time	Master mode	7		
		Slave mode	10		
$t_{a(SO)}$[1][2]	Data output access time	Slave mode		3 x t_{MASTER}	
$t_{dis(SO)}$[1][3]	Data output disable time	Slave mode	25		
$t_{v(SO)}$[1]	Data output valid time	Slave mode (after enable edge)		75	
$t_{v(MO)}$[1]	Data output valid time	Master mode (after enable edge)		30	
$t_{h(SO)}$[1]	Data output hold time	Slave mode (after enable edge)	31		
$t_{h(MO)}$[1]		Master mode (after enable edge)	12		

1. Values based on design simulation and/or characterization results, and not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

Figure 37. SPI timing diagram - slave mode and CPHA = 0

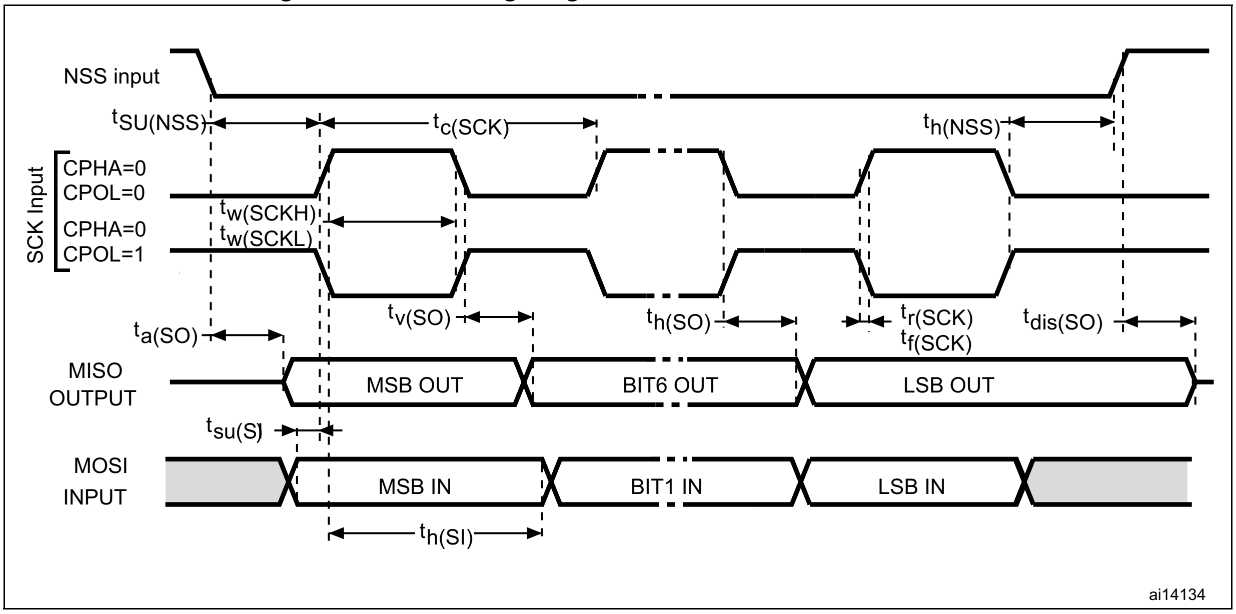
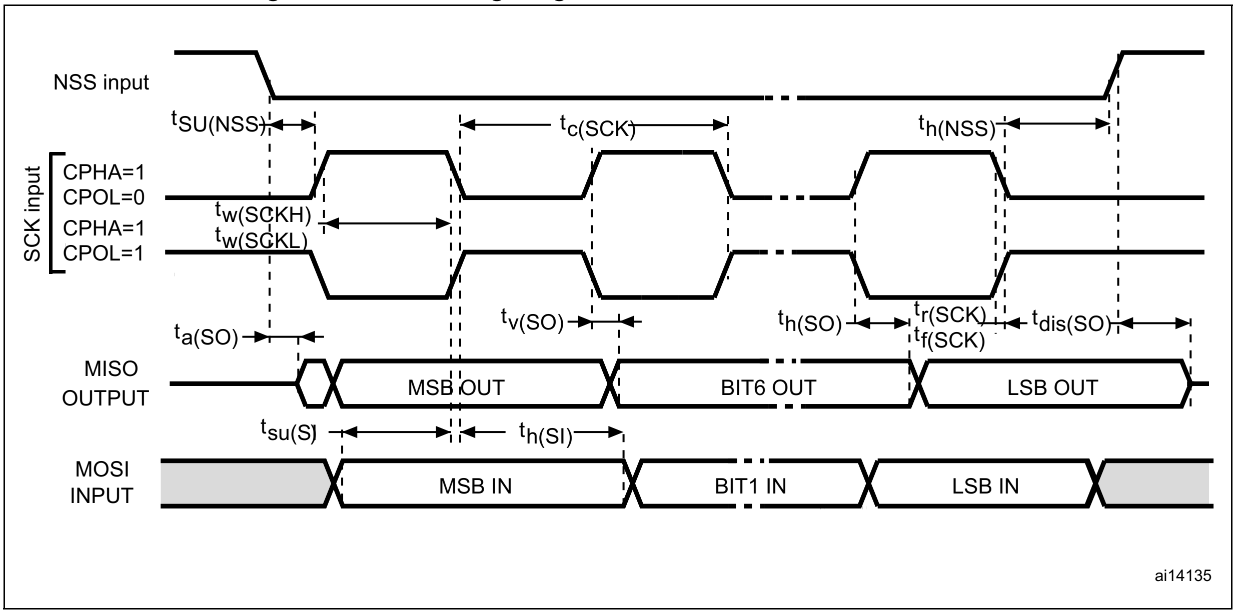


Figure 38. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at CMOS levels: 0.3 V_{DD} and 0.7 V_{DD}.

10.3.10 10-bit ADC characteristics

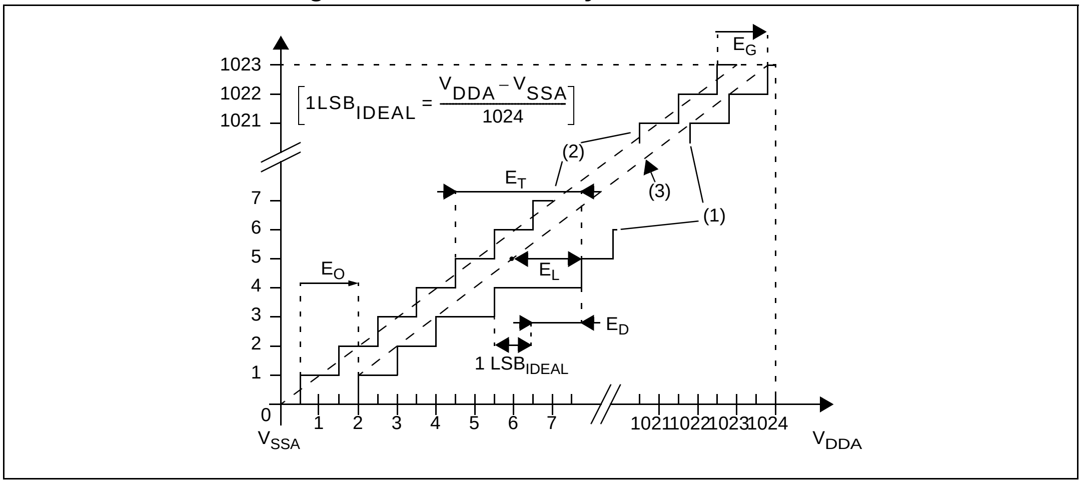
Subject to general operating conditions for V_{DDA}, f_{MASTER}, and T_A unless otherwise specified.

Table 44. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	V_{DDA} = 3 to 5.5 V	1		4	MHz
		V_{DDA} = 4.5 to 5.5 V	1		6	
V_{DDA}	Analog supply		3		5.5	V
V_{REF+}	Positive reference voltage		2.75(1)		V_{DDA}	V
V_{REF-}	Negative reference voltage		V_{SSA}		0.5(1)	V
V_{AIN}	Conversion voltage range(2)		V_{SSA}		V_{DDA}	V
		Devices with external V_{REF+}/V_{REF-} pins	V_{REF-}		V_{REF+}	V
C_{ADC}	Internal sample and hold capacitor			3		pF
t_S(2)	Sampling time	f_{ADC} = 4 MHz		0.75		µs
		f_{ADC} = 6 MHz		0.5		
t_{STAB}	Wakeup time from standby			7		µs
t_{CONV}	Total conversion time (including sampling time, 10-bit resolution)	f_{ADC} = 4 MHz		3.5		µs
		f_{ADC} = 6 MHz		2.33		µs
				14		$1/f_{ADC}$

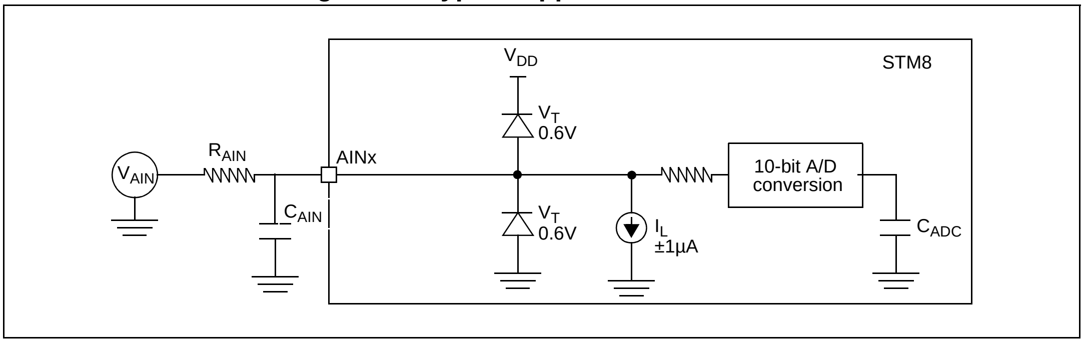
1. Data guaranteed by design, not tested in production.
2. During the sample time the input capacitance C_{AIN} (3 pF max) can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S. After the end of the sample time t_S, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

Figure 41. ADC accuracy characteristics



1. Example of an actual transfer curve.
2. The ideal transfer curve
3. End point correlation line
   E_T = Total unadjusted error: maximum deviation between the actual and the ideal transfer curves.
   E_O = Offset error: deviation between the first actual transition and the first ideal one.
   E_G = Gain error: deviation between the last ideal transition and the last actual one.
   E_D = Differential linearity error: maximum deviation between actual steps and the ideal one.
   E_L = Integral linearity error: maximum deviation between any actual transition and the end point correlation line.

Figure 42. Typical application with ADC



Static latch-up

Two complementary static tests are required on 10 parts to assess the latch-up performance:

- A supply overvoltage (applied to each power supply pin)
- A current injection (applied to each input, output and configurable I/O pin) is performed on each sample.

This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.

Table 50. Electrical sensitivities

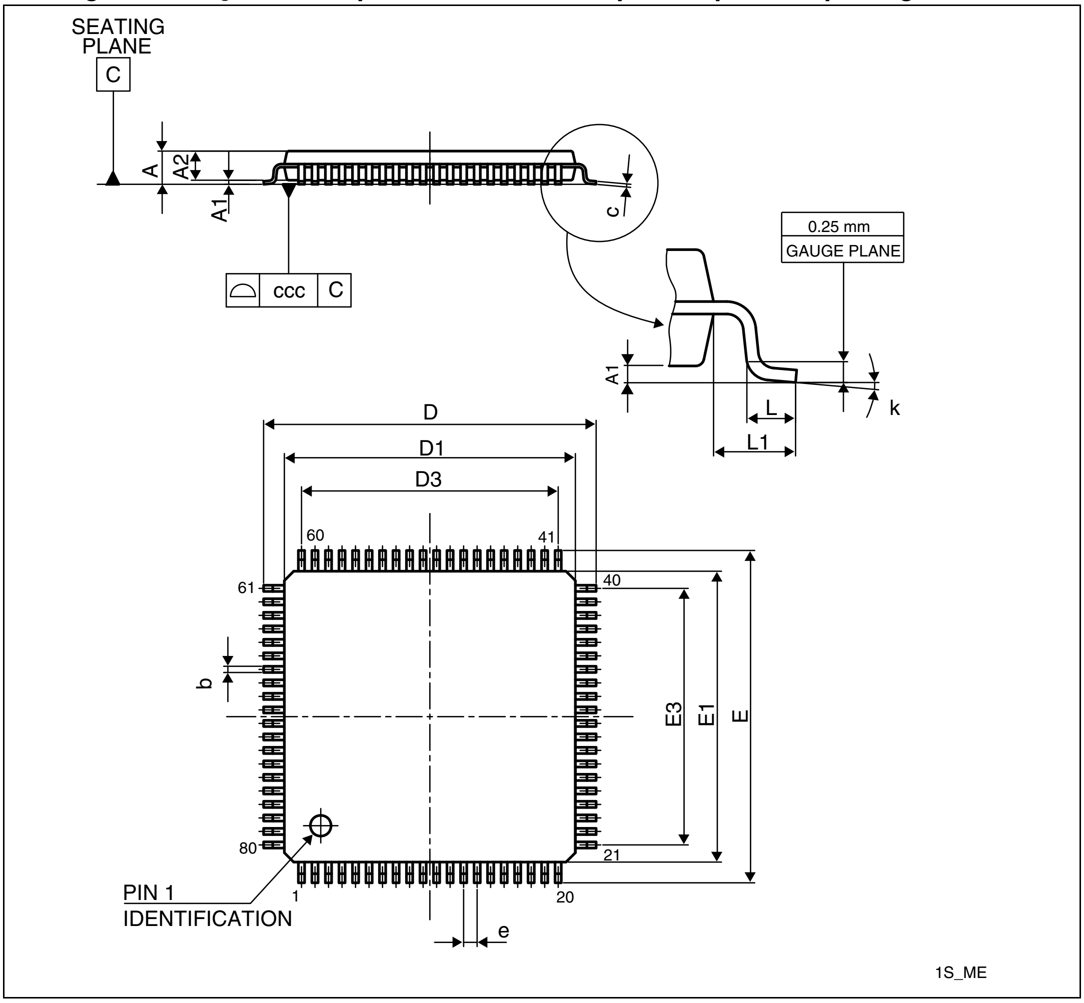
Symbol	Parameter	Conditions	Class(1)
LU	Static latch-up class	$T_A = 25$ °C	A
		$T_A = 85$ °C	A
		$T_A = 125$ °C	A

1. Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to class A it exceeds the JEDEC standard. B class strictly covers all the JEDEC criteria (international standard).

11.1 Package information

11.1.1 LQFP80 package information

Figure 43. LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 51. LQFP80 - 80-pin, 14 x 14 mm low-profile quad flat package mechanical data(1)

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.220	0.320	0.380	0.0087	0.0126	0.0150
c	0.090	-	0.200	0.0035	-	0.0079

11.1.5 LQFP32 package information

Figure 56. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline